

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Battery protection

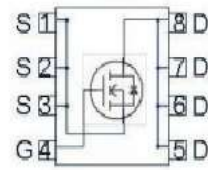
• Ordering Information:

Part NO.	ZMS025N04HN
Marking	ZMS025N04H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

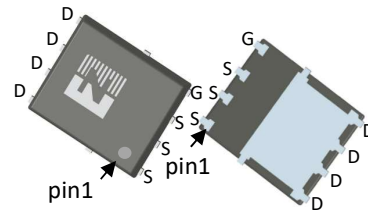
• Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}	$25^{\circ}C \leq T_j \leq 175^{\circ}C$	40	V
Gate-Source Voltage	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	100	A
	I_D	$T_C=75^{\circ}C$	85	A
	I_D	$T_C=100^{\circ}C$	74	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25^{\circ}C$;	400	A
Total Power Dissipation	P_D	$T_C=25^{\circ}C$	68	W
Total Power Dissipation	P_D	$T_A=25^{\circ}C$	3.3	W
Operating Junction Temperature	T_J		-55 to +175	$^{\circ}C$
Storage Temperature	T_{STG}		-55 to +175	$^{\circ}C$
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, VGS=10V, Rg=25 Ω ,	106	mJ
		L=0.5mH, VGS=10V, Rg=25 Ω ,	460	mJ
ESD Level (HBM)	CLASS 2			

• Product Summary



$V_{DS} = 40V$
 $R_{DS(ON)} = 2.5m\Omega$
 $I_D = 100A$



DFN5*6



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	RthJC		-	2.2	°C/W
Thermal resistance, junction-ambient	RthJA ^①		-	45	°C/W
Soldering temperature	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	40			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	2.0	2.7	4.0	V
Drain-Source Leakage Current	I _{DSS}	V _{GS} = 0V, V _{DS} = 40V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 40A		2.5	3	mΩ
Forward Transconductance	g _{FS}	V _{GS} = 5V, I _{SD} = 10A		15		s
Diode Forward Voltage	V _{FSD}	V _{GS} = 0V, I _{SD} = 40A			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V _{DS} = 25V	-	2151	-	pF
Output capacitance	Coss		-	578	-	
Reverse transfer capacitance	Crss		-	24	-	
Gate Resistance	Rg	f = 1MHz	-	2.3		Ω
Total gate charge	Qg	V _{DD} = 15V, I _D = 20A, V _{GS} = 10V	-	33	-	nC
Gate - Source charge	Qgs		-	7.6	-	
Gate - Drain charge	Qgd		-	8.3	-	
Turn-ON Delay time	t _{D(on)}	V _{GS} = 10V, V _{DS} = 15V, R _G = 3.3Ω, I _D = 20A	-	8	-	ns
Turn-ON Rise time	t _r		-	9	-	ns
Turn-Off Delay time	t _{D(off)}		-	14	-	ns
Turn-Off Fall time	t _f		-	9	-	ns
Reverse Recovery Time	t _{RR}	V _{DD} = 20V, di _S /dt = 100A/us, I _S = 50A	-	35	-	ns
Reverse Recovery Charge	Q _{RR}		-	46	-	nC

Fig.1 Gate-Charge Characteristics

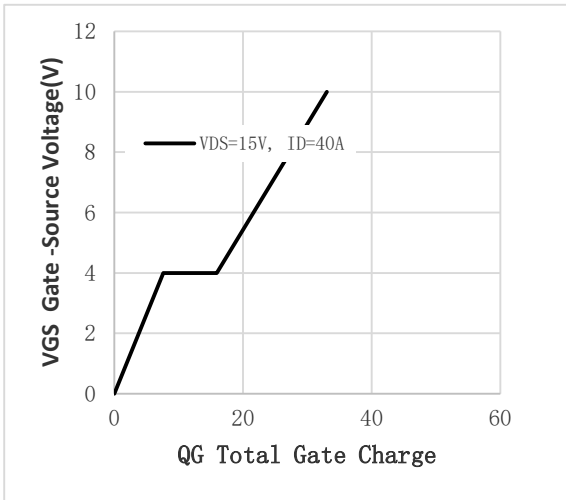


Fig.2 Capacitance Characteristics

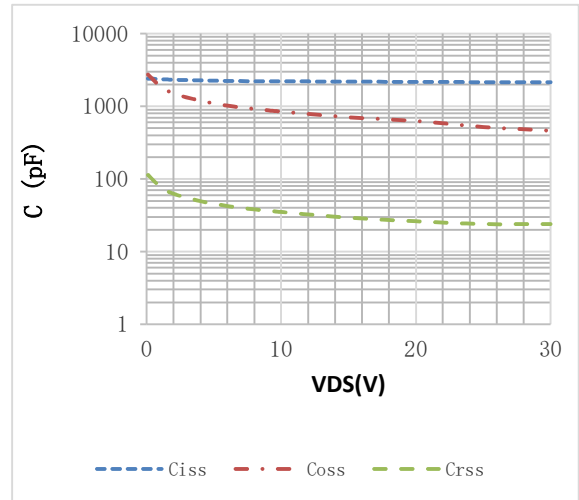


Fig.3 Power Dissipation

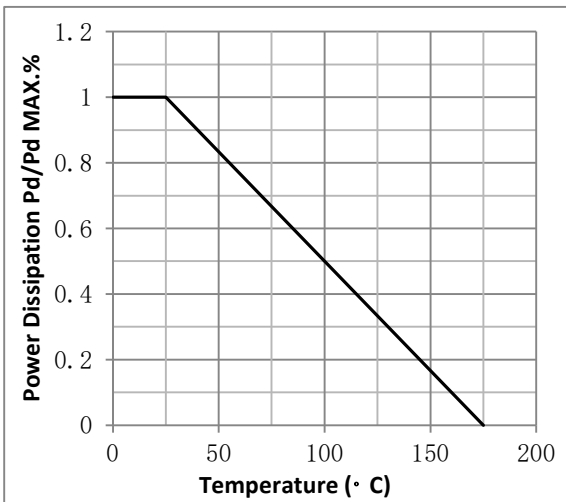


Fig.4 Typical output Characteristics

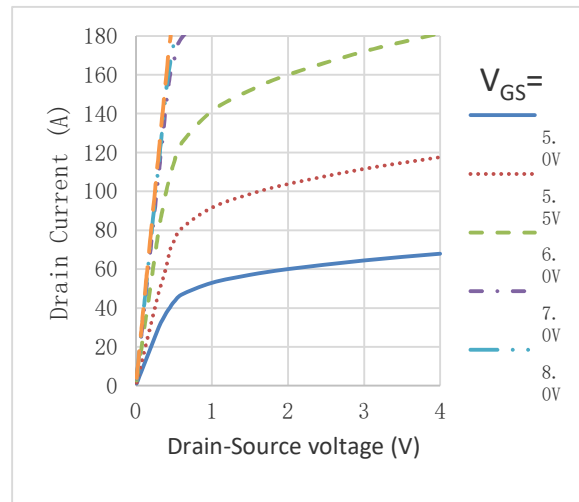


Fig.5 Threshold Voltage V.S Junction Temperature

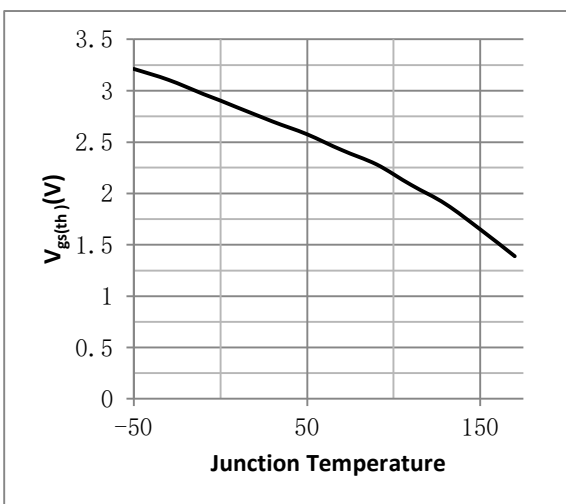


Fig.6 Resistance V.S Drain Current

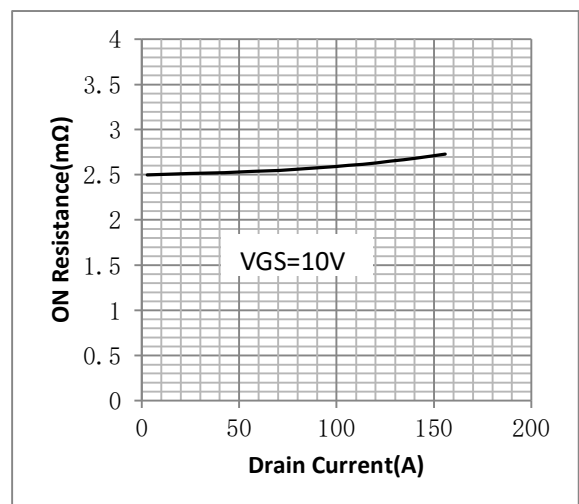


Fig.7 On-Resistance VS Gate Source Voltage

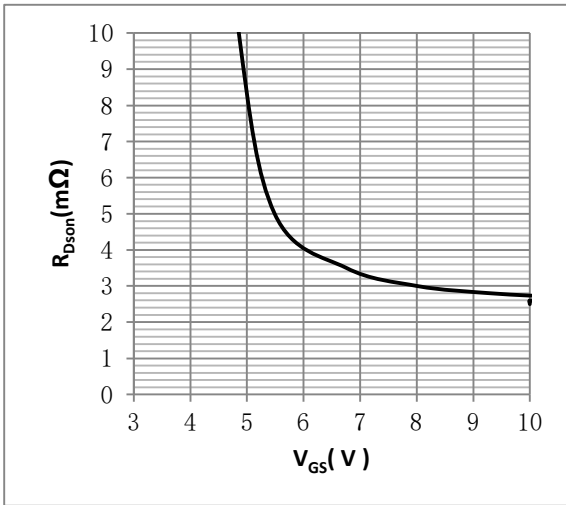


Fig.8 On-Resistance V.S Junction Temperature

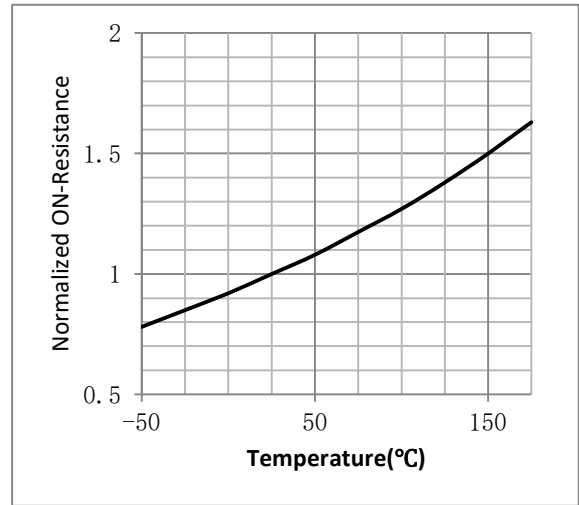


Figure 9. Diode Forward Voltage vs. Current

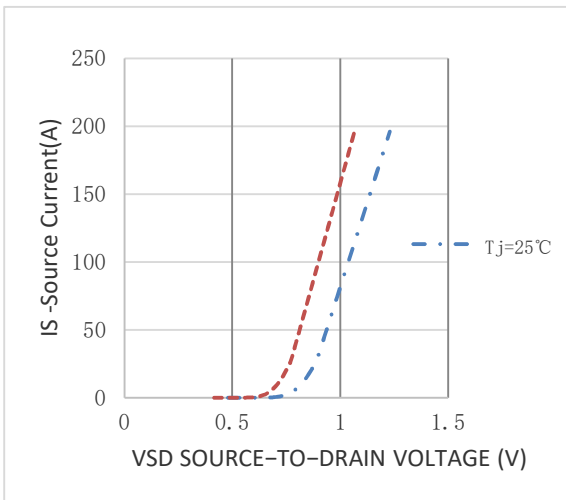


Figure 10. Transfer Characteristics

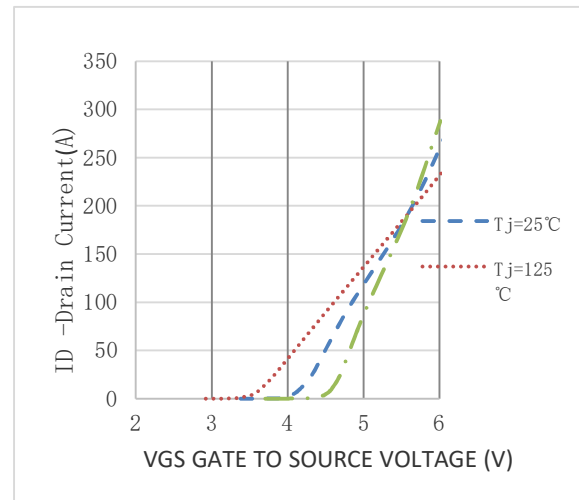


Fig.11 SOA Maximum Safe Operating Area

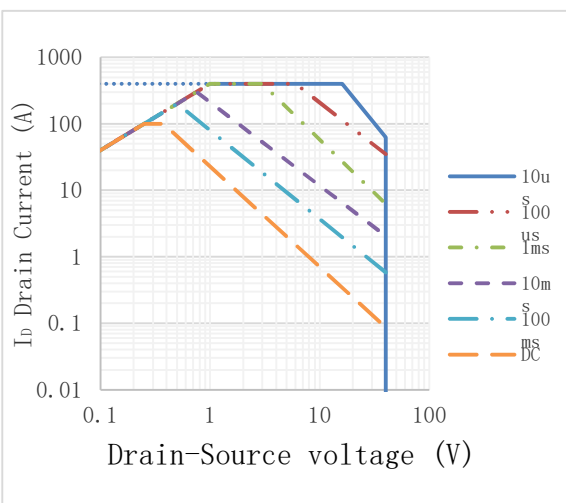
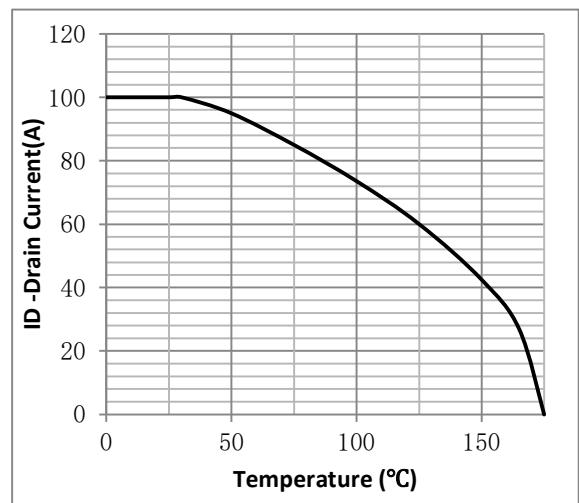
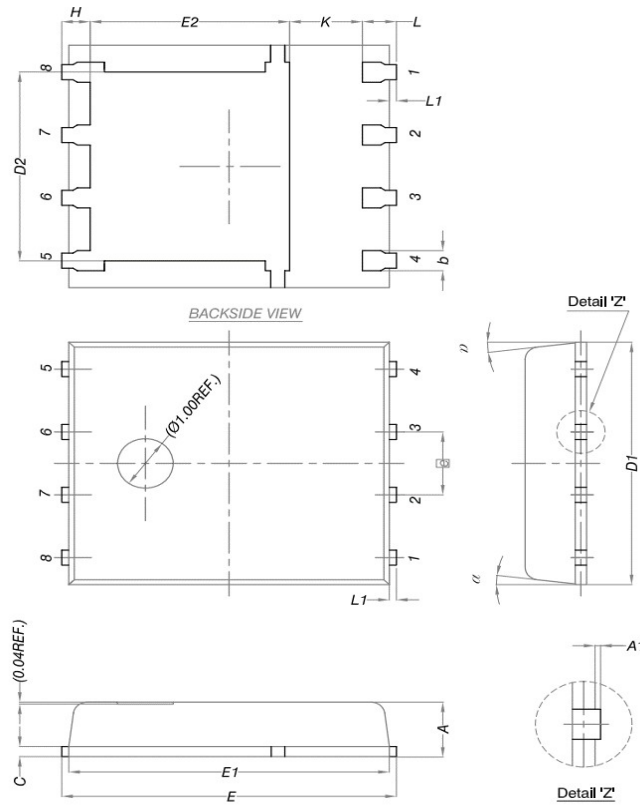


Fig.12 ID vs. Junction Temperature^②



•DFN5*6 Package Outline



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

Note:

- ① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ② Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2022.1.6	
B	2022.9.5	1.Add Reach,HF figure,2.ID modify